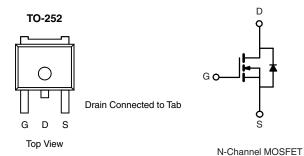


Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0031			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0040			
I _D (A)	50			
Configuration	Single			



FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- AEC-Q101 Qualifiedd
- Material categorization:
 For definitions of compliance please see www.freescale.net.cn



ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD50N03-4m0L-GE3			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current ^a	T _C = 25 °C	ı	50		
	T _C = 125 °C	l _D	50		
Continuous Source Current (Diode Conduction) ^a		Is	50	Α	
Pulsed Drain Current ^b		I _{DM}	125		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	60		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	180	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	136	10/	
	T _C = 125 °C	P_{D}	45	W	
Operating Junction and Storage Temperatur	re Range	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W		
Junction-to-Case (Drain)		R_{thJC}	1.1	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



SQD50N03-4m0L Automotive N-Channel 30 V (D-S) 175 °C MOSFET

SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		30	-	=-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nΑ	
		V _{GS} = 0 V	V _{DS} = 30 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 30 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 30 V, T _J = 175 °C	-	-	150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.0027	0.0031		
Drain-Source On-State Resistance ^a	D	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0048	Ω	
Diain-30dice On-3tate nesistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0056		
		V _{GS} = 4.5 V	I _D = 15 A	-	0.0031	0.0040		
Forward Transconductance ^b	9fs	V _{DS}	V _{DS} = 15 V, I _D = 20 A		122	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	5053	6316	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 15 V, f = 1 MHz	<u>-</u>	921	1151		
Reverse Transfer Capacitance	C _{rss}			-	377	471		
Total Gate Charge ^c	Qg			-	77	116	nC	
Gate-Source Charge ^c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 15 \text{ V}, I_{D} = 50 \text{ A}$	-	14.3	-		
Gate-Drain Charge ^c	Q_{gd}			-	11	-		
Gate Resistance	R_g	f = 1 MHz		1.14	2.28	3.42	Ω	
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD} = 15 \text{ V, R}_L = 0.3 \Omega$ $I_D \cong 50 \text{ A, V}_{GEN} = 10 \text{ V, R}_g = 1 \Omega$		-	10	15	ns	
Rise Time ^c	t _r			-	10	15		
Turn-Off Delay Time ^c	t _{d(off)}			-	42	63		
Fall Time ^c	t _f			-	10	15		
Source-Drain Diode Ratings and Char	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	125	Α	
Forward Voltage	V _{SD}	I _F = 40 A, V _{GS} = 0 V		-	0.85	1.2	V	

Notes

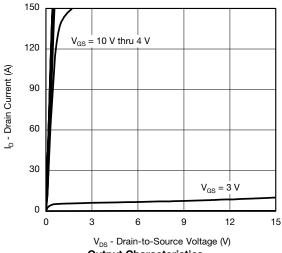
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

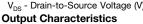
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

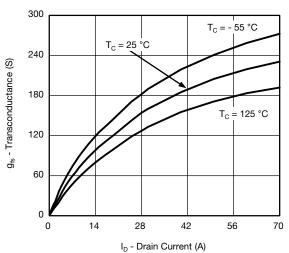


Automotive N-Channel 30 V (D-S) 175 °C MOSFET

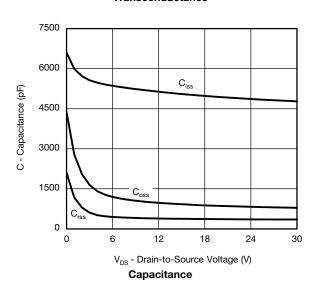
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)





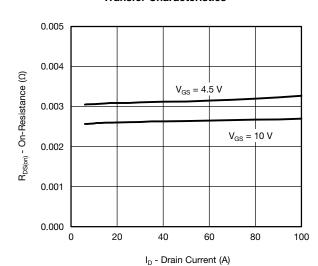


Transconductance

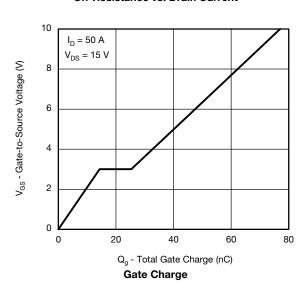


120 96 I_D - Drain Current (A) 72 48 24 T_C = 125°C 55 °C 0 V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics



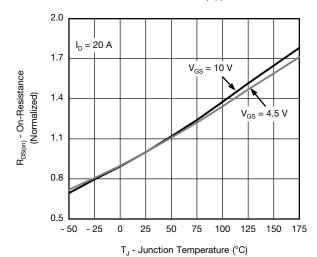
On-Resistance vs. Drain Current



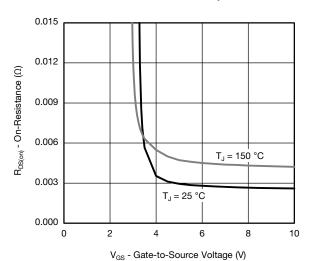


Automotive N-Channel 30 V (D-S) 175 °C MOSFET

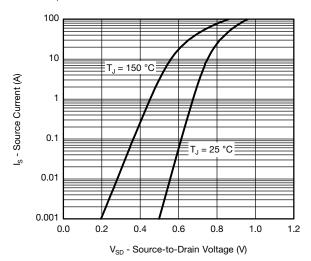
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



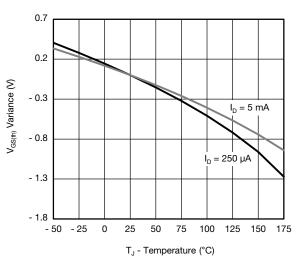
On-Resistance vs. Junction Temperature



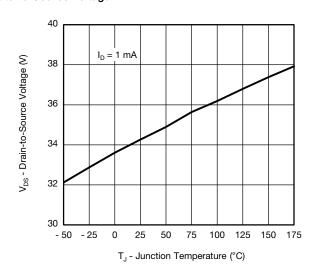
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



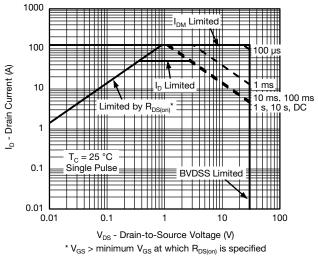
Threshold Voltage



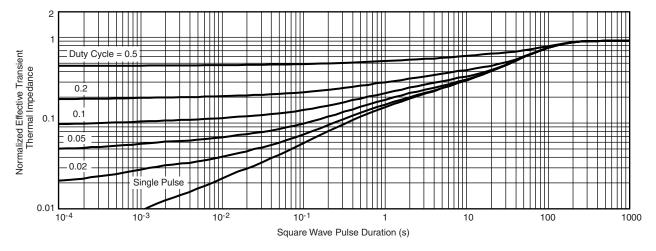
Drain Source Breakdown vs. Junction Temperature

Automotive N-Channel 30 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



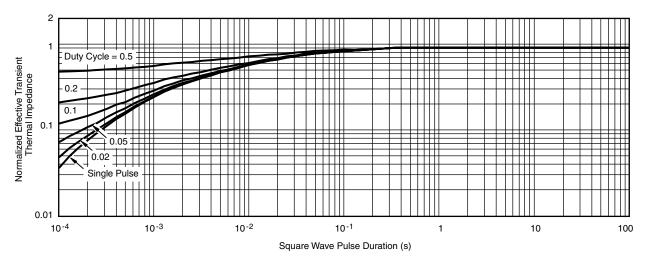
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

Automotive N-Channel 30 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



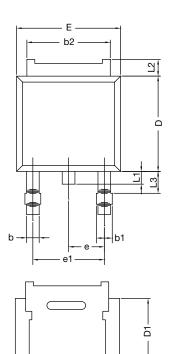
Normalized Thermal Transient Impedance, Junction-to-Case

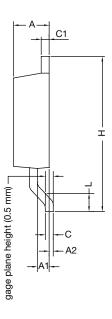
Note

- · The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Automotive N-Channel 30 V (D-S) 175 °C MOSFET

TO-252AA CASE OUTLINE





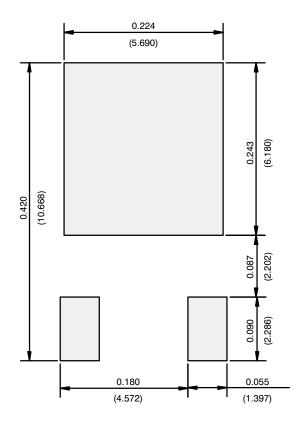
	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28 BSC		0.090 BSC		
e1	4.57 BSC		0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

Note

• Dimension L3 is for reference only.

SQD50N03-4m0LAutomotive N-Channel 30 V (D-S) 175 °C MOSFET

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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SQD50N03-4m0L Automotive N-Channel 30 V (D-S) 175 °C MOSFET

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